

60V, 58A, 8.3mΩ N-channel Power Trench MOSFET
JMTC58N06B
Features

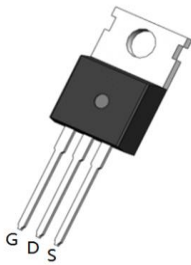
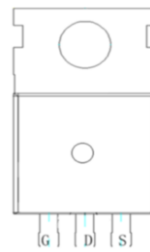
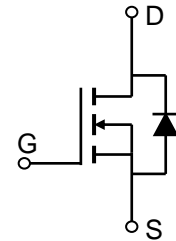
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED
- 100% ΔV_{ds} TESTED
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

- Load Switch
- PWM Application
- Power Management

Product Summary

Parameters	Value	Unit
V_{DSS}	60	V
$V_{GS(th)_{Typ}}$	1.6	V
$I_D(@V_{GS}=10V)$	58	A
$R_{DS(ON)_{Typ}}(@V_{GS}=10V)$	8.3	mΩ


TO-220 Top View

Pin Assignment

Schematic Diagram
Ordering Information

Device	Marking	MSL	Form	Package	Tube(pcs)	Per Carton (pcs)
JMTC58N06B	JMTC58N06B	N/A	Tube	TO-220-3L	50	5000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	58
		$T_C = 100^\circ\text{C}$	41
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	124	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	215
		$T_C = 100^\circ\text{C}$	86
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	68	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.6	



**Electrical Characteristics** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.1	1.6	2.0	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽⁴⁾	$V_{GS} = 10\text{V}, I_D = 30\text{A}$	-	8.3	10.8	m Ω
Dynamic Characteristics						
R_g	Gate Resistance	$f = 1\text{MHz}$	-	2.0	-	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 30\text{V},$ $f = 1\text{MHz}$	-	4032	-	pF
C_{oss}	Output Capacitance		-	186	-	pF
C_{rss}	Reverse Transfer Capacitance		-	152	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 30\text{V}, I_D = 30\text{A}$	-	77	-	nC
Q_{gs}	Gate Source Charge		-	14	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	14	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}, V_{DD} = 30\text{V}$ $I_D = 30\text{A}, R_{GEN} = 3\Omega$	-	10	-	ns
t_r	Turn-On Rise Time		-	27	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	61	-	ns
t_f	Turn-Off Fall Time		-	16	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	58	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	232	A
V_{SD}	Body Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 30\text{A}$	-		1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F = 30\text{A}, di/dt = 100\text{A/us}$	-	25	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	29	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 30\text{V}$, $V_G = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 0.5\text{mH}$, $I_{AS} = 22.26\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. $R_{\theta JA}$ is measured with minimum recommended pad layout.
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.



Typical Performance Characteristics

Figure 1: Power De-rating

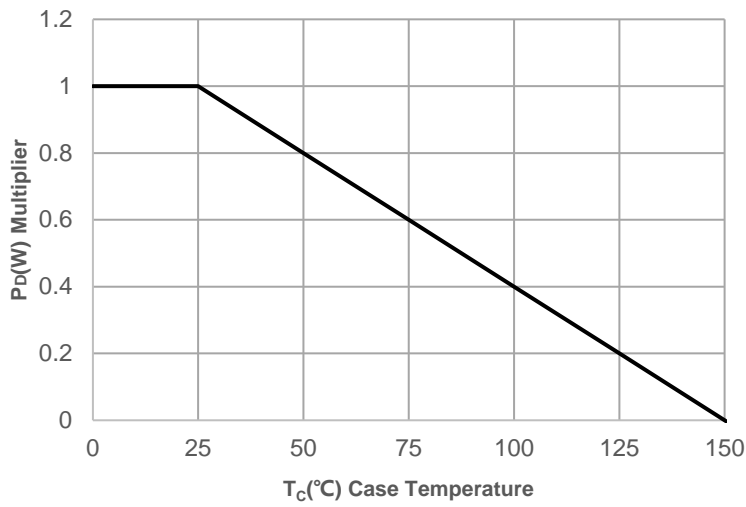


Figure 2: Current De-rating

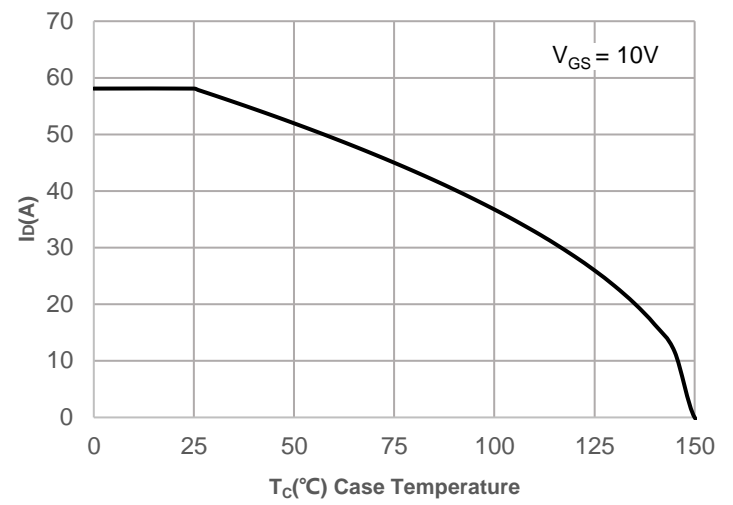


Figure 3: Normalized Maximum Transient Thermal Impedance

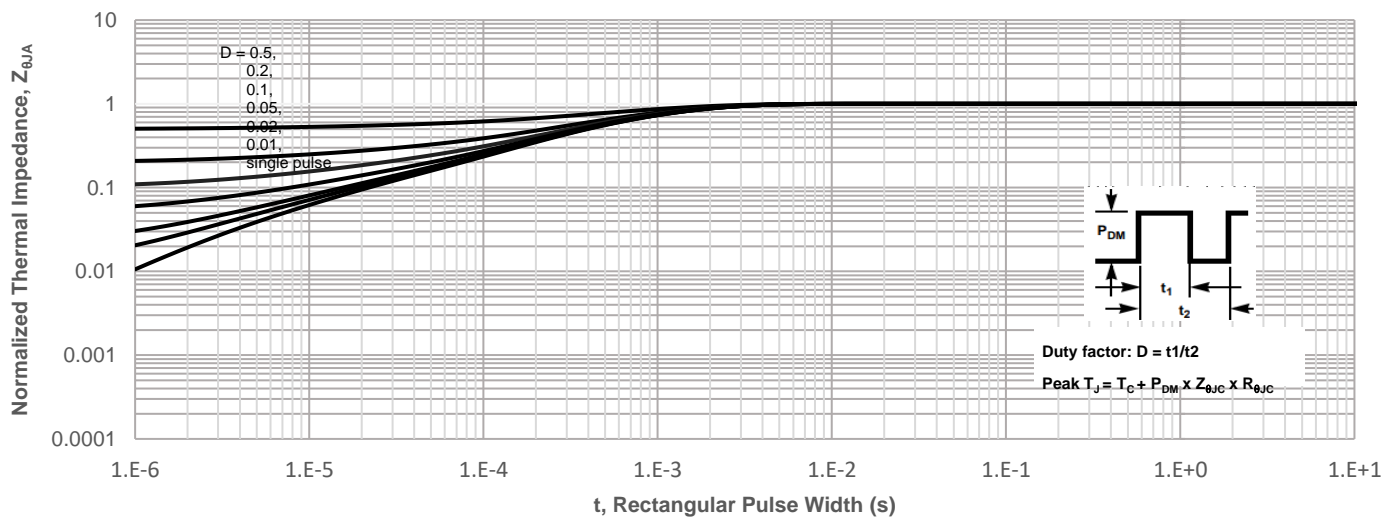
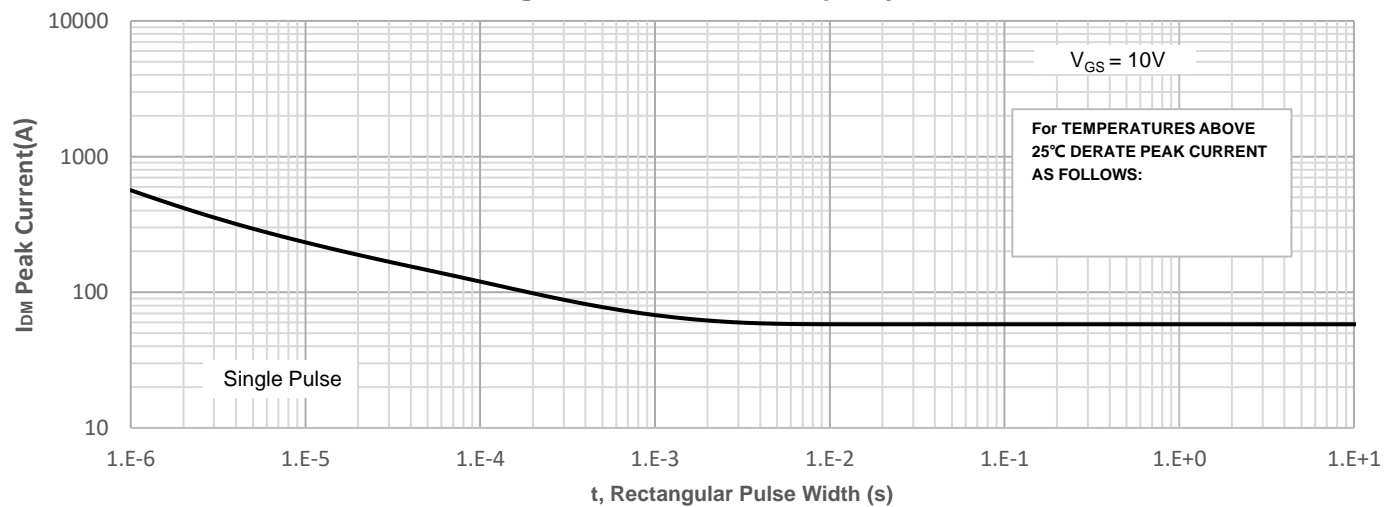
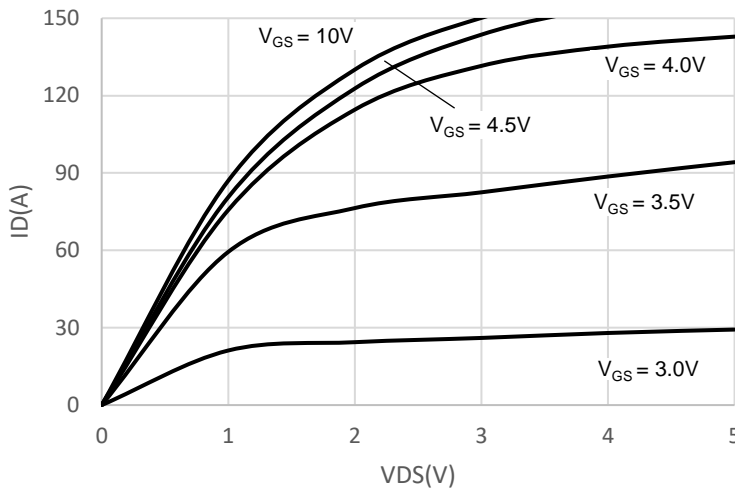
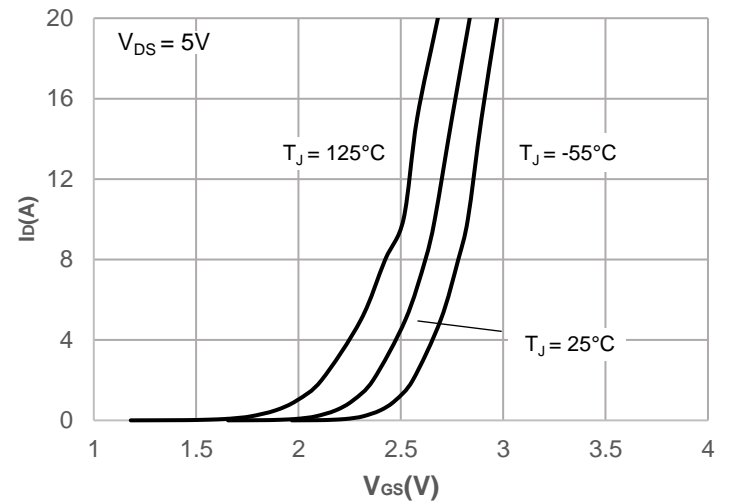
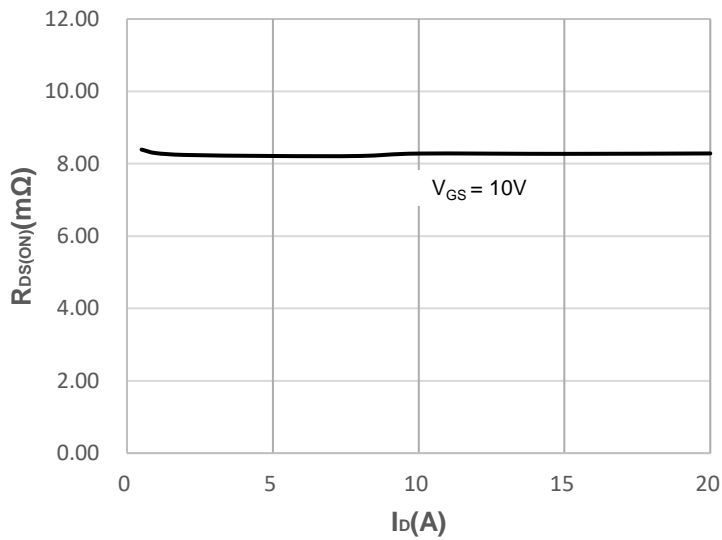
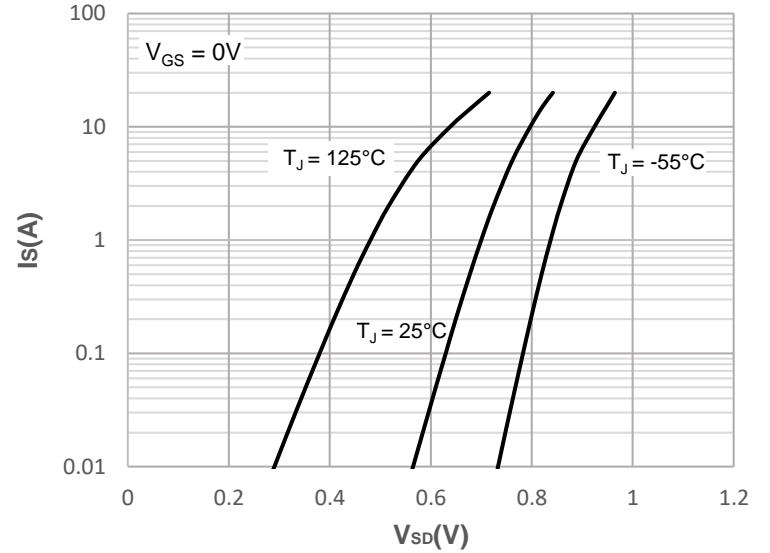
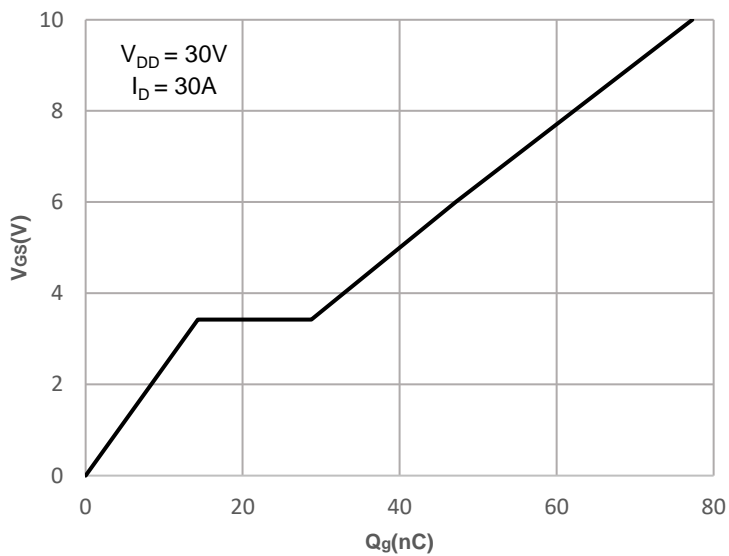
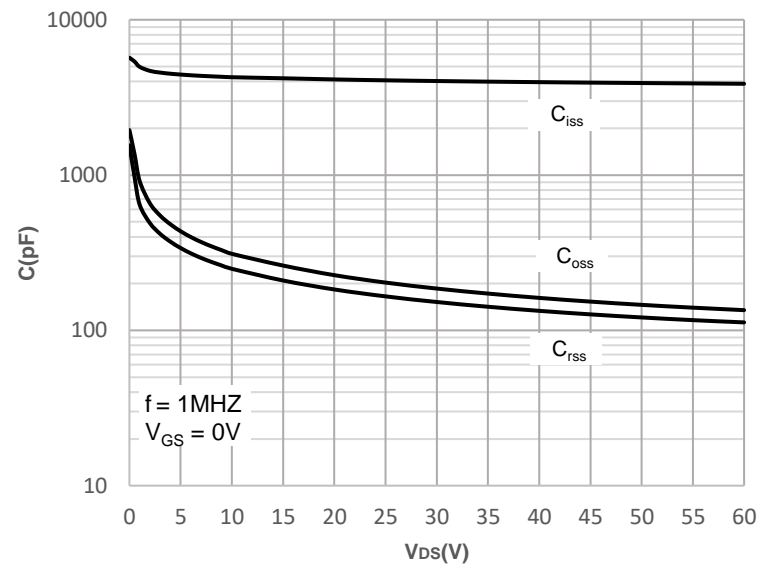


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

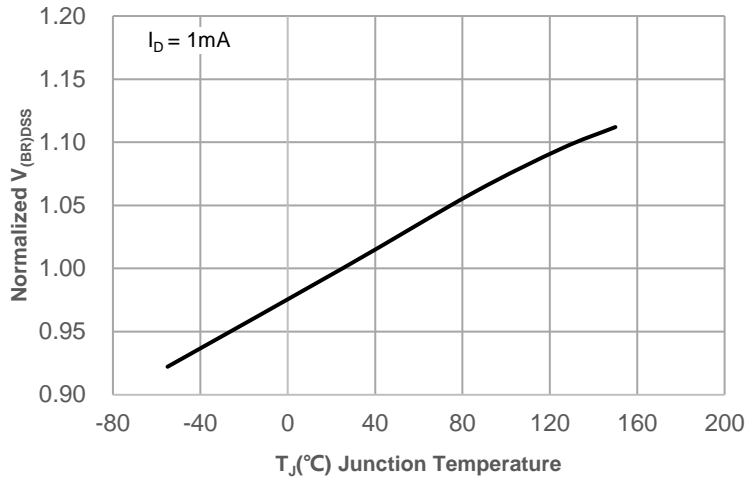


Figure 12: Normalized on Resistance vs. Junction Temperature

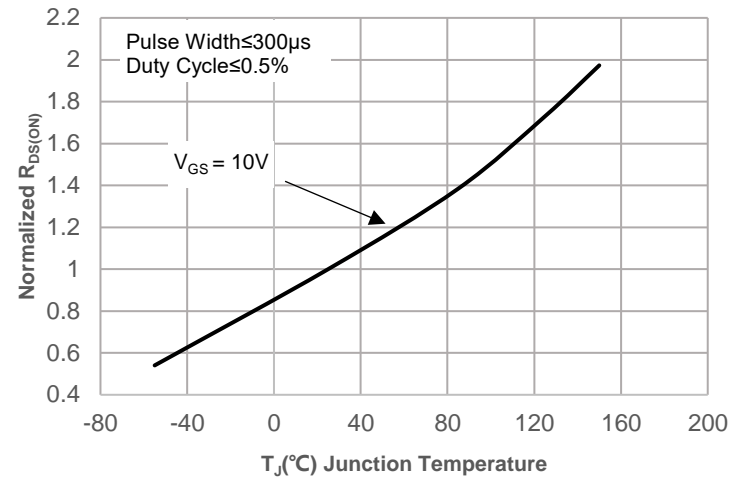


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

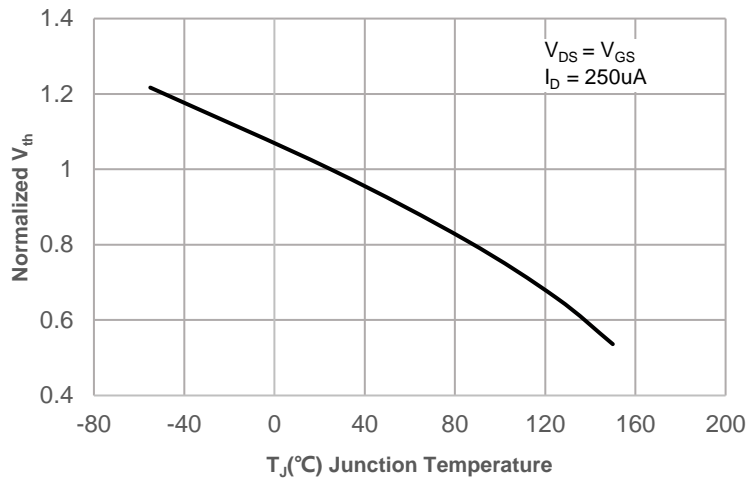


Figure 14: R_{DS(ON)} vs. V_{GS}

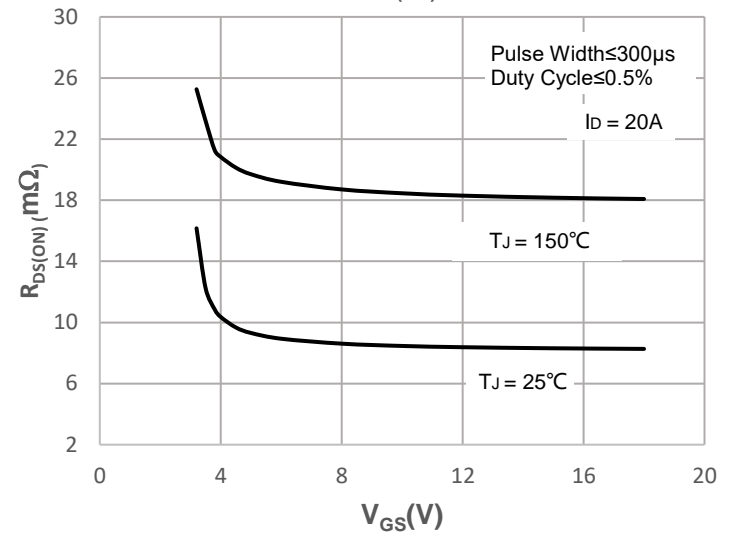
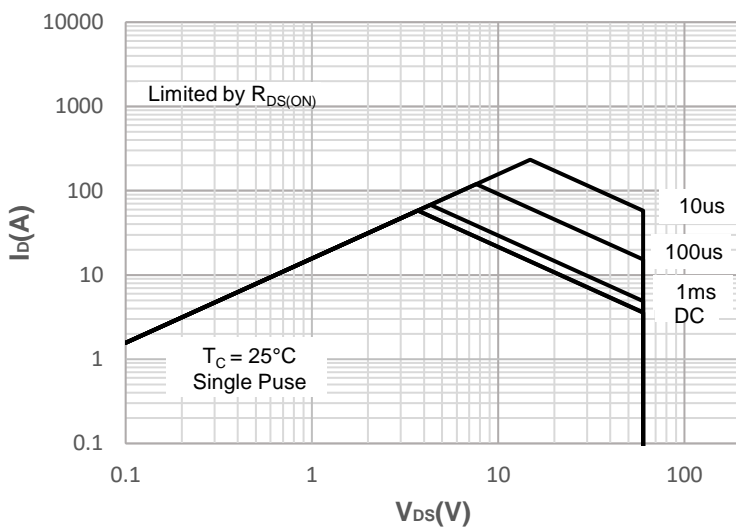


Figure 15: Maximum Safe Operating Area



Test Circuit

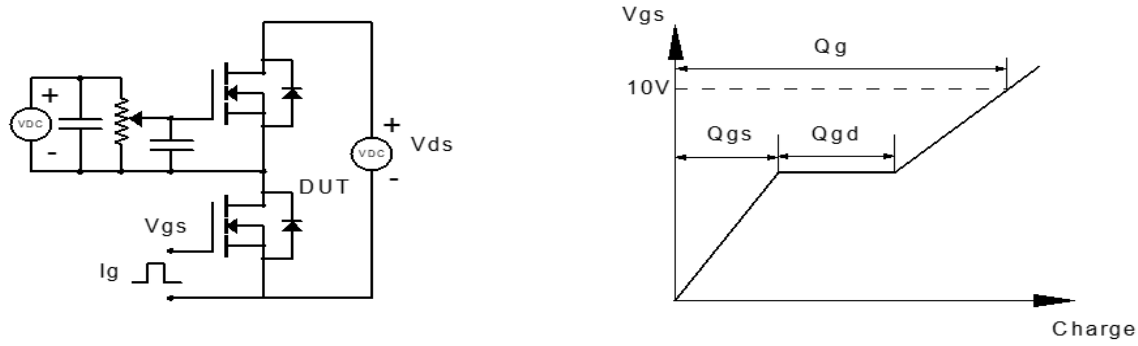


Figure 1: Gate Charge Test Circuit & Waveform

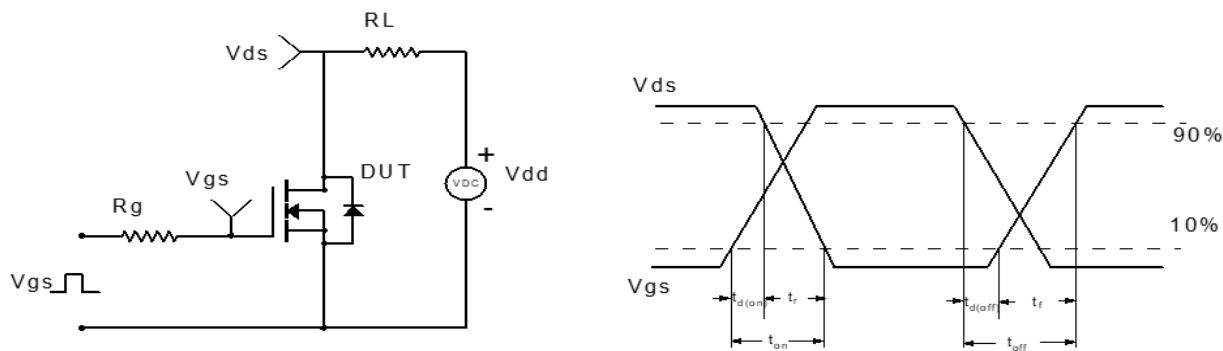


Figure 2: Resistive Switching Test Circuit & Waveform

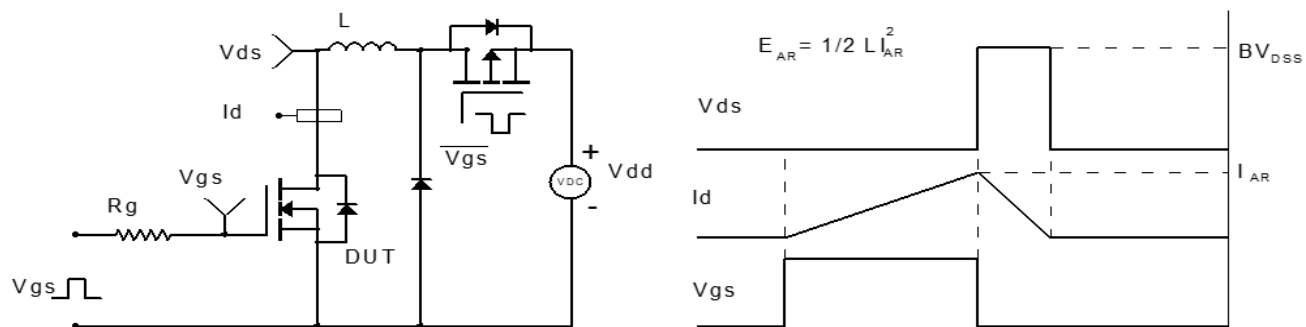


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

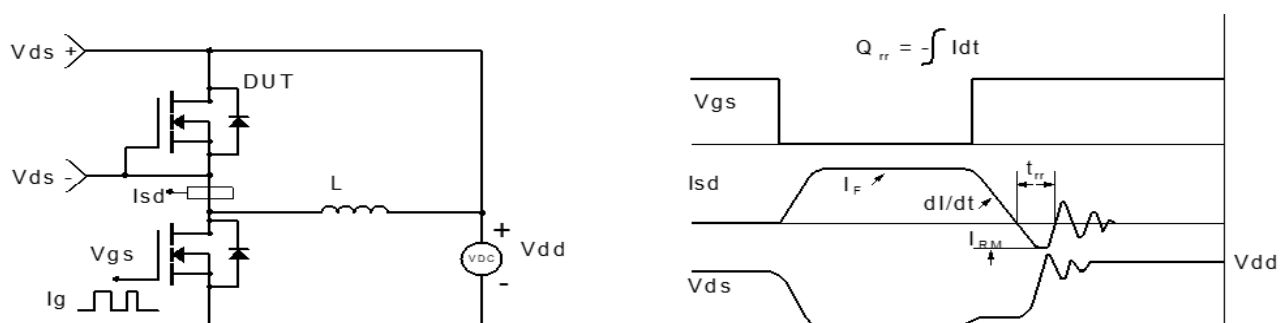
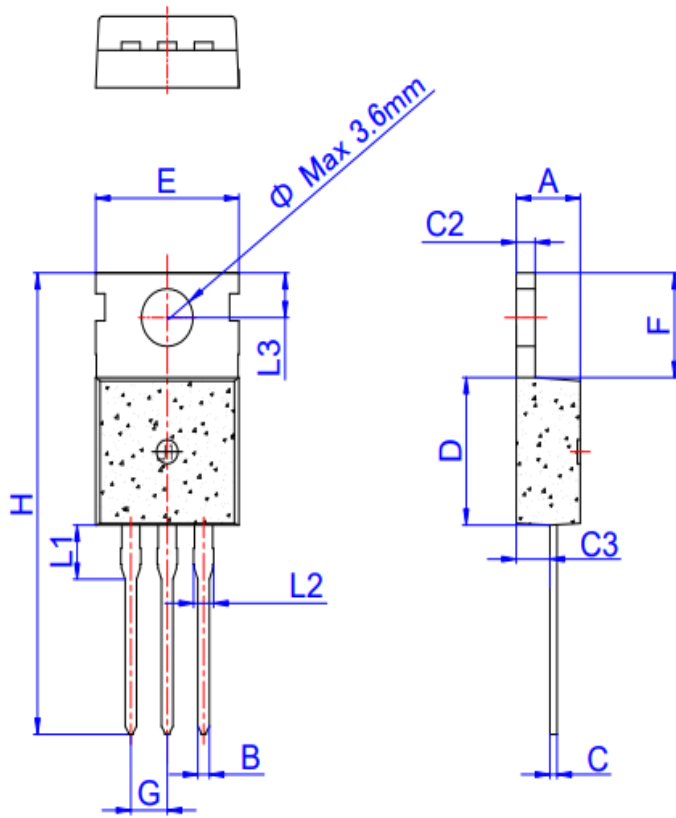


Figure 4: Diode Recovery Test Circuit & Waveform



Package Mechanical Data(TO-220 -3L)

TO-220C

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

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